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November 2015

MOC3081M, MOC3082M, MOC3083M 6-Pin DIP Zero-Cross Triac Driver Optocoupler (800 Volt Peak)

Features

- Simplifies Logic Control of 240 VAC Power
- Zero Voltage Crossing to Minimize Conducted and Radiated Line Noise
- 800 V Peak Blocking Voltage
- Superior Static dv/dt
 - 1500 V/ μ s Typical, 600 V/ μ s Guaranteed
- Safety and Regulatory Approvals
 - UL1577, 4,170 VAC_{RMS} for 1 Minute
 - DIN EN/IEC60747-5-5

Applications

- Solenoid/Valve Controls
- Lighting Controls
- Static Power Switches
- AC Motor Starters
- Temperature Controls
- E.M. Contactors
- AC Motor Drives
- Solid State Relays

Description

The MOC3081M, MOC3082M and MOC3083M devices consist of a GaAs infrared emitting diode optically coupled to a monolithic silicon detector performing the function of a zero voltage crossing bilateral triac driver.

They are designed for use with a discrete power triac in the interface of logic systems to equipment powered from 240 VAC lines, such as solid-state relays, industrial controls, motors, solenoids and consumer appliances, etc.

Schematic

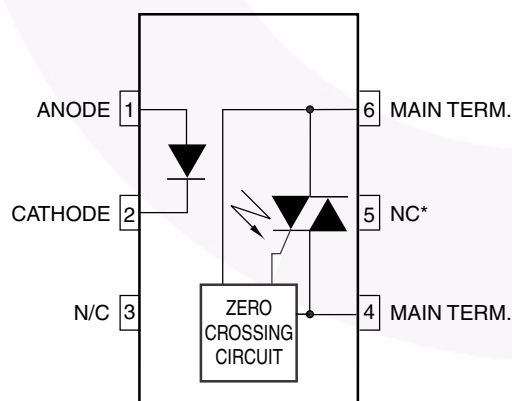


Figure 1. Schematic

Package Outlines

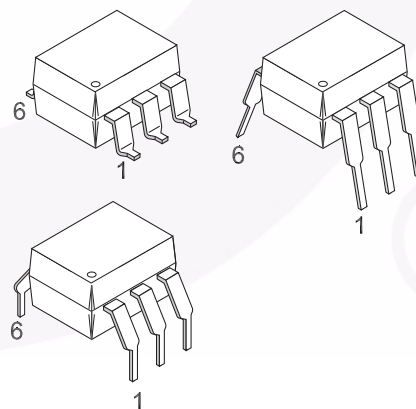


Figure 2. Package Outlines

Safety and Insulation Ratings

As per DIN EN/IEC 60747-5-5, this optocoupler is suitable for “safe electrical insulation” only within the safety limit data. Compliance with the safety ratings shall be ensured by means of protective circuits.

Parameter		Characteristics
Installation Classifications per DIN VDE 0110/1.89 Table 1, For Rated Mains Voltage	< 150 V _{RMS}	I–IV
	< 300 V _{RMS}	I–IV
Climatic Classification		40/85/21
Pollution Degree (DIN VDE 0110/1.89)		2
Comparative Tracking Index		175

Symbol	Parameter	Value	Unit
V _{PR}	Input-to-Output Test Voltage, Method A, V _{IORM} × 1.6 = V _{PR} , Type and Sample Test with t _m = 10 s, Partial Discharge < 5 pC	1360	V _{peak}
	Input-to-Output Test Voltage, Method B, V _{IORM} × 1.875 = V _{PR} , 100% Production Test with t _m = 1 s, Partial Discharge < 5 pC	1594	V _{peak}
V _{IORM}	Maximum Working Insulation Voltage	850	V _{peak}
V _{IOTM}	Highest Allowable Over-Voltage	6000	V _{peak}
	External Creepage	≥ 7	mm
	External Clearance	≥ 7	mm
	External Clearance (for Option TV, 0.4" Lead Spacing)	≥ 10	mm
DTI	Distance Through Insulation (Insulation Thickness)	≥ 0.5	mm
R _{IO}	Insulation Resistance at T _S , V _{IO} = 500 V	> 10 ⁹	Ω

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. $T_A = 25^\circ\text{C}$ unless otherwise specified.

Symbol	Parameter	Value	Unit
TOTAL DEVICE			
T_{STG}	Storage Temperature	-40 to +150	$^\circ\text{C}$
T_{OPR}	Operating Temperature	-40 to +85	$^\circ\text{C}$
T_J	Junction Temperature Range	-40 to +100	$^\circ\text{C}$
T_{SOL}	Lead Solder Temperature	260 for 10 seconds	$^\circ\text{C}$
P_D	Total Device Power Dissipation at 25°C Ambient	250	mW
	Derate Above 25°C	2.94	mW/ $^\circ\text{C}$
EMITTER			
I_F	Continuous Forward Current	60	mA
V_R	Reverse Voltage	6	V
P_D	Total Power Dissipation at 25°C Ambient	120	mW
	Derate Above 25°C	1.41	mW/ $^\circ\text{C}$
DETECTOR			
V_{DRM}	Off-State Output Terminal Voltage	800	V
I_{TSM}	Peak Non-Repetitive Surge Current (Single Cycle 60 Hz Sine Wave)	1	A
P_D	Total Power Dissipation at 25°C Ambient	150	mW
	Derate Above 25°C	1.76	mW/ $^\circ\text{C}$

Electrical Characteristics

$T_A = 25^\circ\text{C}$ unless otherwise specified.

Individual Component Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
EMITTER						
V_F	Input Forward Voltage	$I_F = 30\text{ mA}$		1.3	1.5	V
I_R	Reverse Leakage Current	$V_R = 6\text{ V}$		0.005	100	μA
DETECTOR						
I_{DRM1}	Peak Blocking Current, Either Direction	$V_{\text{DRM}} = 800\text{ V}$, $I_F = 0^{(1)}$		10	500	nA
dv/dt	Critical Rate of Rise of Off-State Voltage	$I_F = 0$ (Figure 11) ⁽²⁾	600	1500		$\text{V}/\mu\text{s}$

Transfer Characteristics

Symbol	Parameter	Test Conditions	Device	Min.	Typ.	Max.	Unit
I_{FT}	LED Trigger Current (Rated I_{FT})	Main Terminal Voltage = $3\text{ V}^{(3)}$	MOC3081M			15	mA
			MOC3082M			10	
			MOC3083M			5	
V_{TM}	Peak On-State Voltage, Either Direction	$I_{\text{TM}} = 100\text{ mA peak}$, $I_F = \text{rated } I_{\text{FT}}$	All		1.8	3.0	V
I_H	Holding Current, Either Direction		All		500		μA

Zero Crossing Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_{INH}	Inhibit Voltage (MT1-MT2 voltage above which device will not trigger)	$I_F = \text{Rated } I_{\text{FT}}$		12	20	V
I_{DRM2}	Leakage in Inhibited State	$I_F = \text{Rated } I_{\text{FT}}$, $V_{\text{DRM}} = 600\text{ V}$, off-state			2	mA

Isolation Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_{ISO}	Isolation Voltage ⁽⁴⁾	$f = 60\text{ Hz}$, $t = 1\text{ Minute}$	4170			VAC_{RMS}
R_{ISO}	Isolation Resistance	$V_{\text{I-O}} = 500\text{ V}_{\text{DC}}$		10^{11}		Ω
C_{ISO}	Isolation Capacitance	$V = 0\text{ V}$, $f = 1\text{ MHz}$		0.2		pF

Notes:

- Test voltage must be applied within dv/dt rating.
- This is static dv/dt . See Figure 11 for test circuit. Commutating dv/dt is a function of the load-driving thyristor(s) only.
- All devices are guaranteed to trigger at an I_F value less than or equal to max I_{FT} . Therefore, recommended operating I_F lies between max I_{FT} (15 mA for MOC3081M, 10 mA for MOC3082M, 5 mA for MOC3083M) and absolute maximum I_F (60 mA).
- Isolation voltage, V_{ISO} , is an internal device dielectric breakdown rating. For this test, pins 1 and 2 are common, and pins 4, 5 and 6 are common.

Typical Performance Curves

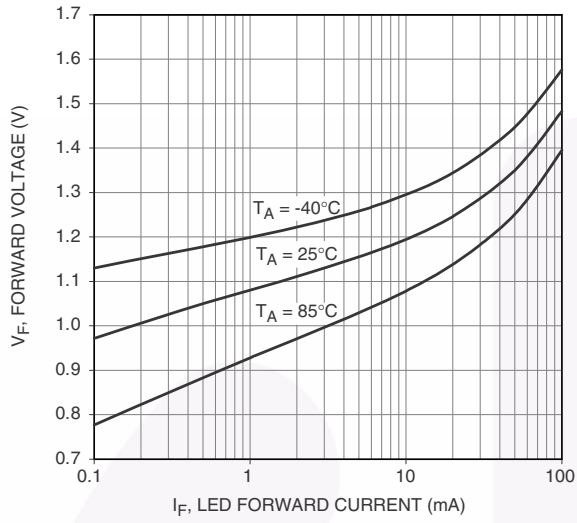


Figure 3. LED Forward Voltage vs. Forward Current

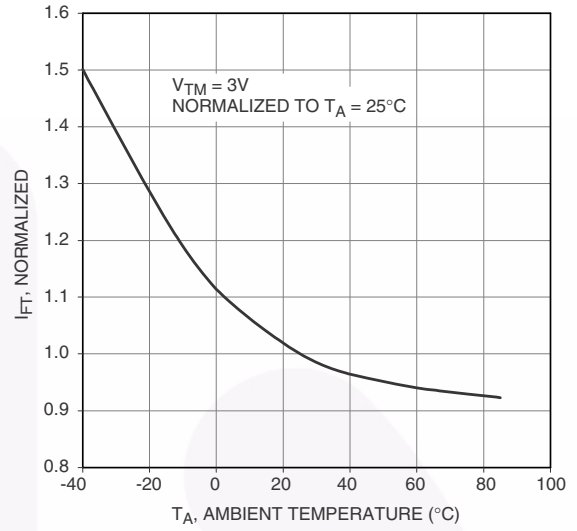


Figure 4. Trigger Current vs. Temperature

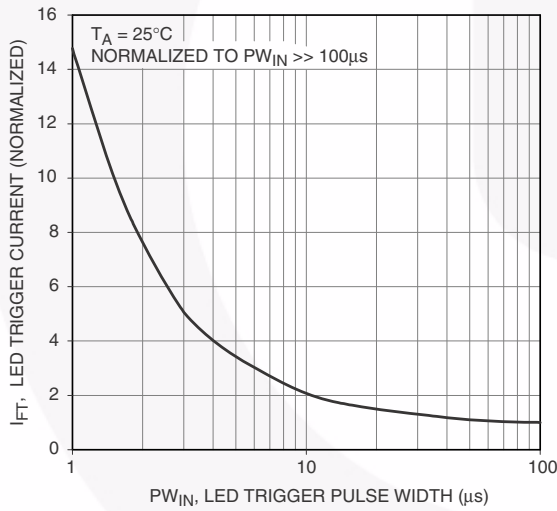


Figure 5. LED Current Required to Trigger vs. LED Pulse Width

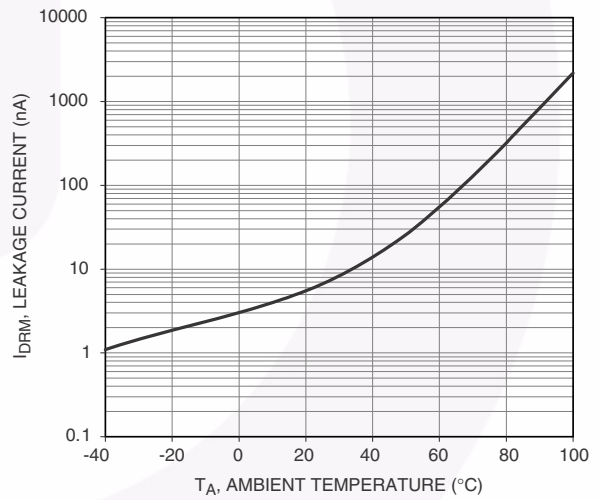


Figure 6. Leakage Current, I_{DRM} vs. Temperature

Typical Performance Curves (Continued)

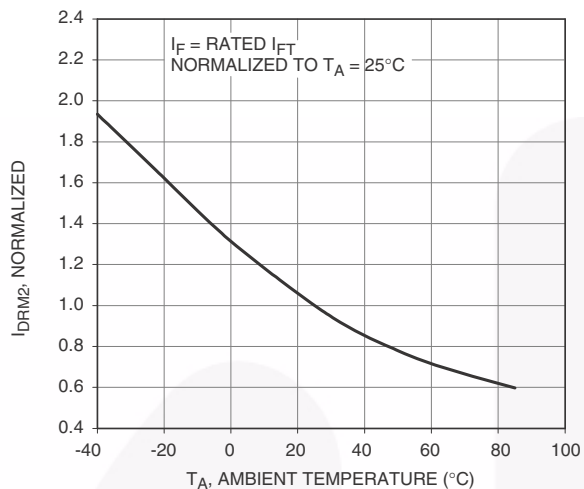


Figure 7. I_{DRM2} , Leakage in Inhibit State vs. Temperature

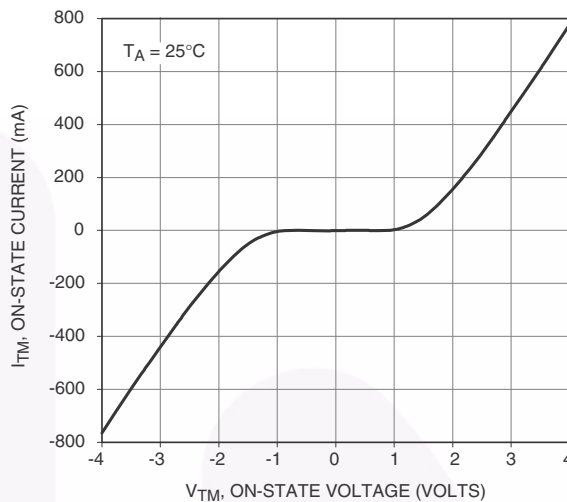


Figure 8. On-State Characteristics

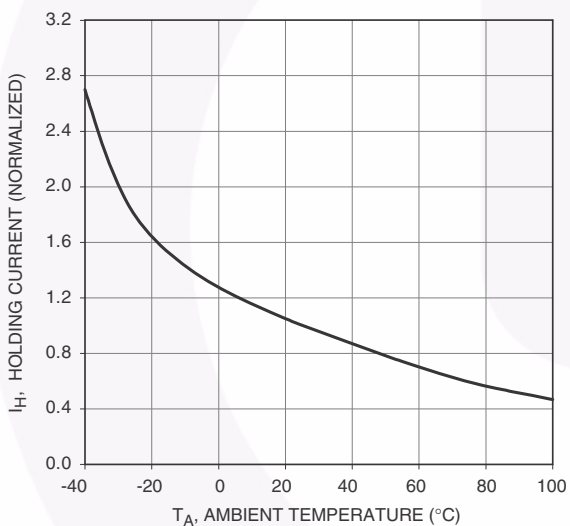


Figure 9. I_H , Holding Current vs. Temperature

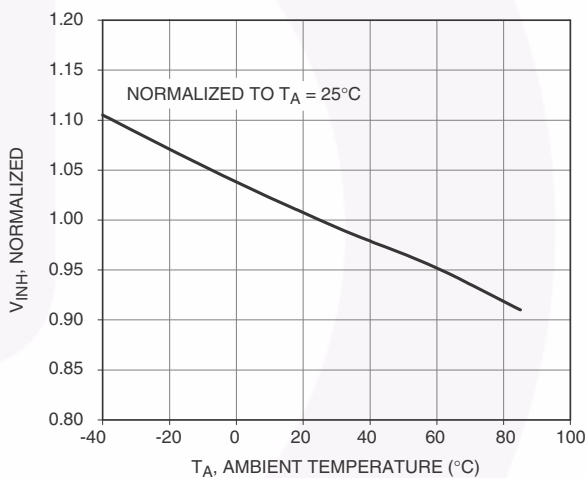


Figure 10. Inhibit Voltage vs. Temperature

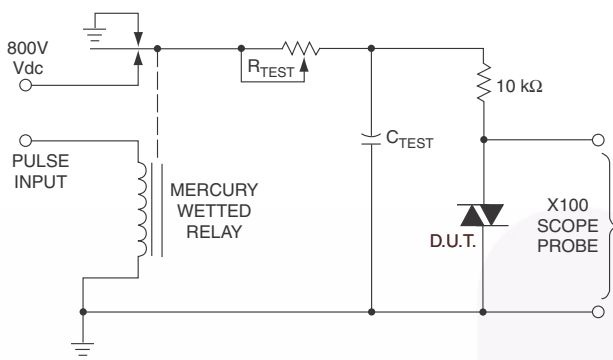


Figure 11. Static dv/dt Test Circuit

1. The mercury wetted relay provides a high speed repeated pulse to the D.U.T.
2. 100x scope probes are used, to allow high speeds and voltages.
3. The worst-case condition for static dv/dt is established by triggering the D.U.T. with a normal LED input current, then removing the current. The variable R_{TEST} allows the dv/dt to be gradually increased until the D.U.T. continues to trigger in response to the applied voltage pulse, even after the LED current has been removed. The dv/dt is then decreased until the D.U.T. stops triggering. τ_{RC} is measured at this point and recorded.

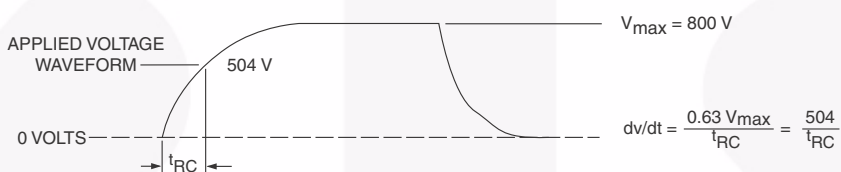
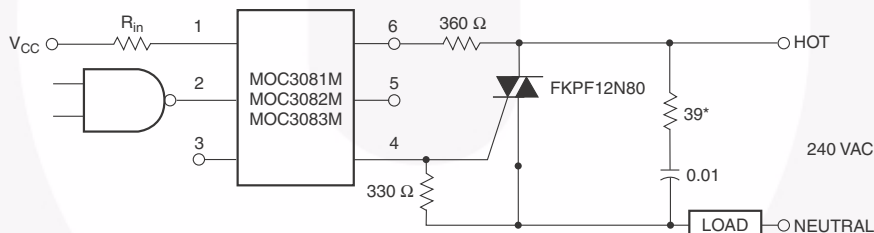


Figure 12. Static dv/dt Test Waveform

Typical circuit for use when hot line switching is required. In this circuit the “hot” side of the line is switched and the load connected to the cold or neutral side. The load may be connected to either the neutral or hot line.

R_{in} is calculated so that I_F is equal to the rated I_{FT} of the part, 15 mA for the MOC3081M, 10 mA for the MOC3082M, and 5 mA for the MOC3083M. The 39 Ω resistor and 0.01 μF capacitor are for snubbing of the triac and may or may not be necessary depending upon the particular triac and load use.



* For highly inductive loads (power factor < 0.5), change this value to 360 Ω .

Figure 13. Hot-Line Switching Application Circuit

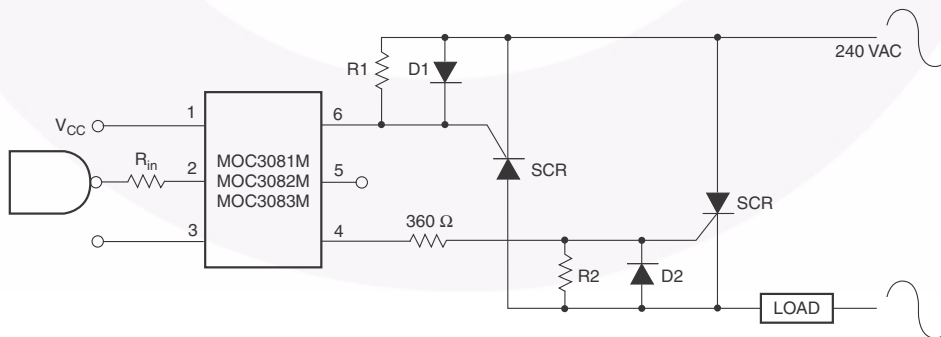


Figure 14. Inverse-Parallel SCR Driver Circuit

Suggested method of firing two, back-to-back SCR's with a Fairchild triac driver. Diodes can be 1N4001; resistors, R1 and R2, are optional 330 Ω .

Note: This optoisolator should not be used to drive a load directly. It is intended to be a trigger device only.

Reflow Profile



Profile Feature	Pb-Free Assembly Profile
Temperature Minimum (T _{smin})	150°C
Temperature Maximum (T _{smax})	200°C
Time (t _s) from (T _{smin} to T _{smax})	60 seconds to 120 seconds
Ramp-up Rate (T _L to T _P)	3°C/second maximum
Liquidous Temperature (T _L)	217°C
Time (t _L) Maintained Above (T _L)	60 seconds to 150 seconds
Peak Body Package Temperature	260°C +0°C / -5°C
Time (t _p) within 5°C of 260°C	30 seconds
Ramp-down Rate (T _P to T _L)	6°C/second maximum
Time 25°C to Peak Temperature	8 minutes maximum

Figure 15. Reflow Profile

Ordering Information⁽⁵⁾

Part Number	Package	Packing Method
MOC3081M	DIP 6-Pin	Tube (50 Units)
MOC3081SM	SMT 6-Pin (Lead Bend)	Tube (50 Units)
MOC3081SR2M	SMT 6-Pin (Lead Bend)	Tape and Reel (1000 Units)
MOC3081VM	DIP 6-Pin, DIN EN/IEC60747-5-5 Option	Tube (50 Units)
MOC3081SVM	SMT 6-Pin (Lead Bend), DIN EN/IEC60747-5-5 Option	Tube (50 Units)
MOC3081SR2VM	SMT 6-Pin (Lead Bend), DIN EN/IEC60747-5-5 Option	Tape and Reel (1000 Units)
MOC3081TVM	DIP 6-Pin, 0.4" Lead Spacing, DIN EN/IEC60747-5-5 Option	Tube (50 Units)

Note:

5. The product orderable part number system listed in this table also applies to the MOC3082M, and MOC3083M, product families.

Marking Information

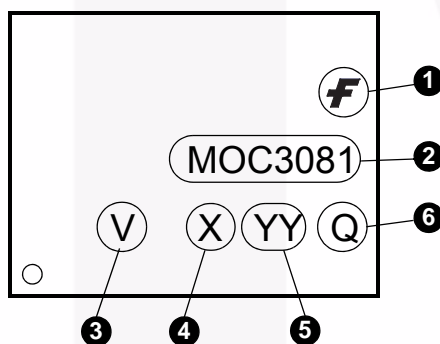


Figure 16. Top Mark

Top Mark Definitions	
1	Fairchild Logo
2	Device Number
3	DIN EN/IEC60747-5-5 Option (only appears on component ordered with this option)
4	One-Digit Year Code, e.g., '5'
5	Two-Digit Work Week, Ranging from '01' to '53'
6	Assembly Package Code



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